AMD Xilinx - XCV812E-6BG560C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	4704
Number of Logic Elements/Cells	21168
Total RAM Bits	1146880
Number of I/O	404
Number of Gates	254016
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	560-LBGA Exposed Pad, Metal
Supplier Device Package	560-MBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xcv812e-6bg560c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1: **Virtex-E Extended Memory Field-Programmable Gate Array Family Members**

Device	Logic Gates	CLB Array	Logic Cells	Differential I/O Pairs	User I/O	BlockRAM Bits	Distributed RAM Bits
XCV405E	129,600	40 x 60	10,800	183	404	573,440	153,600
XCV812E	254,016	56 x 84	21,168	201	556	1,146,880	301,056

Virtex-E Compared to Virtex Devices

The Virtex-E family offers up to 43,200 logic cells in devices up to 30% faster than the Virtex family.

I/O performance is increased to 622 Mb/s using Source Synchronous data transmission architectures and synchronous system performance up to 240 MHz using singled-ended SelectI/O technology. Additional I/O standards are supported, notably LVPECL, LVDS, and BLVDS, which use two pins per signal. Almost all signal pins can be used for these new standards.

Virtex-E devices have up to 640 Kb of faster (250MHz) block SelectRAM, but the individual RAMs are the same size and structure as in the Virtex family. They also have eight DLLs instead of the four in Virtex devices. Each individual DLL is slightly improved with easier clock mirroring and 4x frequency multiplication.

V_{CCINT}, the supply voltage for the internal logic and memory, is 1.8 V, instead of 2.5 V for Virtex devices. Advanced processing and 0.18 µm design rules have resulted in smaller dice, faster speed, and lower power consumption.

I/O pins are 3 V tolerant, and can be 5 V tolerant with an external 100 Ω resistor. PCI 5 V is not supported. With the addition of appropriate external resistors, any pin can tolerate any voltage desired.

Banking rules are different. With Virtex devices, all input buffers are powered by V_{CCINT}. With Virtex-E devices, the LVTTL, LVCMOS2, and PCI input buffers are powered by the I/O supply voltage V_{CCO}.

The Virtex-E family is not bitstream-compatible with the Virtex family, but Virtex designs can be compiled into equivalent Virtex-E devices.

The same device in the same package for the Virtex-E and Virtex families are pin-compatible with some minor exceptions. See the data sheet pinout section for details.

General Description

The Virtex-E FPGA family delivers high-performance, high-capacity programmable logic solutions. Dramatic increases in silicon efficiency result from optimizing the new architecture for place-and-route efficiency and exploiting an aggressive 6-layer metal 0.18 µm CMOS process. These advances make Virtex-E FPGAs powerful and flexible alternatives to mask-programmed gate arrays. The Virtex-E family includes the nine members in Table 1.

Building on experience gained from Virtex FPGAs, the Virtex-E family is an evolutionary step forward in programmable logic design. Combining a wide variety of programmable system features, a rich hierarchy of fast, flexible interconnect resources, and advanced process technology, the Virtex-E family delivers a high-speed and high-capacity programmable logic solution that enhances design flexibility while reducing time-to-market.

Virtex-E Architecture

Virtex-E devices feature a flexible, regular architecture that comprises an array of configurable logic blocks (CLBs) surrounded by programmable input/output blocks (IOBs), all interconnected by a rich hierarchy of fast, versatile routing resources. The abundance of routing resources permits the Virtex-E family to accommodate even the largest and most complex designs.

Virtex-E FPGAs are SRAM-based, and are customized by loading configuration data into internal memory cells. Configuration data can be read from an external SPROM (master serial mode), or can be written into the FPGA (SelectMAP™, slave serial, and JTAG modes).

The standard Xilinx Foundation Series™ and Alliance Series™ Development systems deliver complete design support for Virtex-E, covering every aspect from behavioral and schematic entry, through simulation, automatic design translation and implementation, to the creation and downloading of a configuration bit stream.

Higher Performance

Virtex-E devices provide better performance than previous generations of FPGAs. Designs can achieve synchronous system clock rates up to 240 MHz including I/O or 622 Mb/s using Source Synchronous data transmission architectures. Virtex-E I/Os comply fully with 3.3 V PCI specifications, and interfaces can be implemented that operate at 33 MHz or 66 MHz.

While performance is design-dependent, many designs operate internally at speeds in excess of 133 MHz and can achieve over 311 MHz. Table 2, page 3, shows performance data for representative circuits, using worst-case timing parameters.

Table 1: **Supported I/O Standards**

I/O Standard	Output V_{CCO}	Input V_{CCO}	Input V_{REF}	Board Termination Voltage (V_{TT})
LVTTL	3.3	3.3	N/A	N/A
LVCMOS2	2.5	2.5	N/A	N/A
LVCMOS18	1.8	1.8	N/A	N/A
SSTL3 I & II	3.3	N/A	1.50	1.50
SSTL2 I & II	2.5	N/A	1.25	1.25
GTL	N/A	N/A	0.80	1.20
GTL+	N/A	N/A	1.0	1.50
HSTL I	1.5	N/A	0.75	0.75
HSTL III & IV	1.5	N/A	0.90	1.50
CTT	3.3	N/A	1.50	1.50
AGP-2X	3.3	N/A	1.32	N/A
PCI33_3	3.3	3.3	N/A	N/A
PCI66_3	3.3	3.3	N/A	N/A
BLVDS & LVDS	2.5	N/A	N/A	N/A
LVPECL	3.3	N/A	N/A	N/A

In addition to the CLK and CE control signals, the three flip-flops share a Set/Reset (SR). For each flip-flop, this signal can be independently configured as a synchronous Set, a synchronous Reset, an asynchronous Preset, or an asynchronous Clear.

The output buffer and all of the IOB control signals have independent polarity controls.

All pads are protected against damage from electrostatic discharge (ESD) and from over-voltage transients. After configuration, clamping diodes are connected to V_{CCO} with the exception of LVCMOS18, LVCMOS25, GTL, GTL+, LVDS, and LVPECL.

Optional pull-up, pull-down and weak-keeper circuits are attached to each pad. Prior to configuration all outputs not involved in configuration are forced into their high-impedance state. The pull-down resistors and the weak-keeper circuits are inactive, but IOs can optionally be pulled up.

The activation of pull-up resistors prior to configuration is controlled on a global basis by the configuration mode pins. If the pull-up resistors are not activated, all the pins are in a high-impedance state. Consequently, external pull-up or pull-down resistors must be provided on pins required to be at a well-defined logic level prior to configuration.

All Virtex-E IOBs support IEEE 1149.1-compatible boundary scan testing.

Input Path

The Virtex-E IOB input path routes the input signal directly to internal logic and/ or through an optional input flip-flop.

An optional delay element at the D-input of this flip-flop eliminates pad-to-pad hold time. The delay is matched to the internal clock-distribution delay of the FPGA, and when used, assures that the pad-to-pad hold time is zero.

Each input buffer can be configured to conform to any of the low-voltage signalling standards supported. In some of these standards the input buffer utilizes a user-supplied threshold voltage, V_{REF} The need to supply V_{REF} imposes constraints on which standards can be used in close proximity to each other. See "I/O Banking" on page 2.

There are optional pull-up and pull-down resistors at each user I/O input for use after configuration. Their value is in the range 50 - 100 kΩ.

Output Path

The output path includes a 3-state output buffer that drives the output signal onto the pad. The output signal can be routed to the buffer directly from the internal logic or through an optional IOB output flip-flop.

The 3-state control of the output can also be routed directly from the internal logic or through a flip-flip that provides synchronous enable and disable.

Each output driver can be individually programmed for a wide range of low-voltage signalling standards. Each output buffer can source up to 24 mA and sink up to 48 mA. Drive strength and slew rate controls minimize bus transients.

In most signalling standards, the output High voltage depends on an externally supplied V_{CCO} voltage. The need to supply V_{CCO} imposes constraints on which standards can be used in close proximity to each other. See "I/O Banking" on page 2.

An optional weak-keeper circuit is connected to each output. When selected, the circuit monitors the voltage on the pad and weakly drives the pin High or Low to match the input signal. If the pin is connected to a multiple-source signal, the weak keeper holds the signal in its last state if all drivers are disabled. Maintaining a valid logic level in this way eliminates bus chatter.

Since the weak-keeper circuit uses the IOB input buffer to monitor the input level, an appropriate V_{REF} voltage must be provided if the signalling standard requires one. The provision of this voltage must comply with the I/O banking rules.

I/O Banking

Some of the I/O standards described above require V_{CCO} and/or V_{REF} voltages. These voltages are externally supplied and connected to device pins that serve groups of tions and the desired performance. Finally, the router interconnects the blocks.

The PAR algorithms support fully automatic implementation of most designs. For demanding applications, however, the user can exercise various degrees of control over the process. User partitioning, placement, and routing information is optionally specified during the design-entry process. The implementation of highly structured designs can benefit greatly from basic floor planning.

The implementation software incorporates Timing Wizard® timing-driven placement and routing. Designers specify timing requirements along entire paths during design entry. The timing path analysis routines in PAR then recognize these user-specified requirements and accommodate them.

Timing requirements are entered on a schematic in a form directly relating to the system requirements, such as the targeted clock frequency, or the maximum allowable delay between two registers. In this way, the overall performance of the system along entire signal paths is automatically tailored to user-generated specifications. Specific timing information for individual nets is unnecessary.

Design Verification

In addition to conventional software simulation, FPGA users can use in-circuit debugging techniques. Because Xilinx devices are infinitely reprogrammable, designs can be verified in real time without the need for extensive sets of software simulation vectors.

The development system supports both software simulation and in-circuit debugging techniques. For simulation, the system extracts the post-layout timing information from the design database, and back-annotates this information into the net list for use by the simulator. Alternatively, the user can verify timing-critical portions of the design using the TRCE® static timing analyzer.

For in-circuit debugging, an optional download and readback cable is available. This cable connects the FPGA in the target system to a PC or workstation. After downloading the design into the FPGA, the designer can single-step the logic, readback the contents of the flip-flops, and so observe the internal logic state. Simple modifications can be downloaded into the system in a matter of minutes.

Configuration

Virtex-E devices are configured by loading configuration data into the internal configuration memory. Note that attempting to load an incorrect bitstream causes configuration to fail and can damage the device.

Some of the pins used for configuration are dedicated pins, while others can be re-used as general purpose inputs and outputs once configuration is complete.

The following are dedicated pins:

- Mode pins (M2, M1, M0)
- Configuration clock pin (CCLK)
- $\overline{\text{PROGRAM}}$ pin
- DONE pin
- Boundary-scan pins (TDI, TDO, TMS, TCK)

Depending on the configuration mode chosen, CCLK can be an output generated by the FPGA, or it can be generated externally and provided to the FPGA as an input. The $\overline{\text{PROGRAM}}$ pin must be pulled High prior to reconfiguration.

Note that some configuration pins can act as outputs. For correct operation, these pins require a V_{CCO} of 3.3 V to permit LVTTL operation. All of the pins affected are in banks 2 or 3. The configuration pins needed for SelectMap (CS, Write) are located in bank 1.

Configuration Modes

Virtex-E supports the following four configuration modes.

- Slave-serial mode
- Master-serial mode
- SelectMAP mode
- Boundary-scan mode (JTAG)

The Configuration mode pins (M2, M1, M0) select among these configuration modes with the option in each case of having the IOB pins either pulled up or left floating prior to configuration. The selection codes are listed in Table 8.

Configuration through the boundary-scan port is always available, independent of the mode selection. Selecting the boundary-scan mode simply turns off the other modes. The three mode pins have internal pull-up resistors, and default to a logic High if left unconnected. However, it is recommended to drive the configuration mode pins externally.

Table 8: **Configuration Codes**

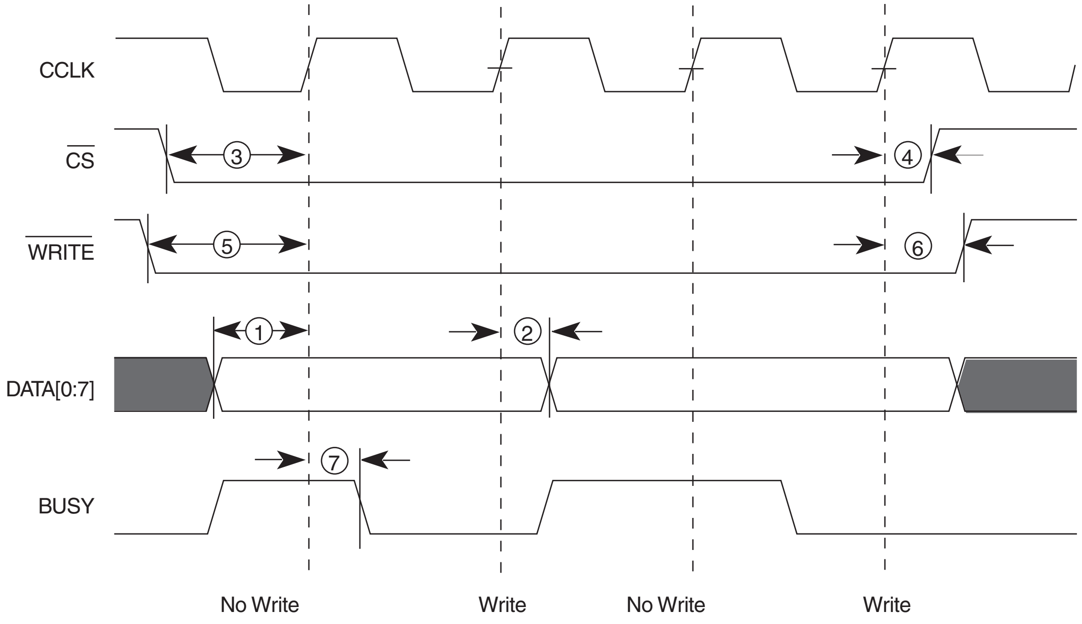
Configuration Mode	M2	M1	M0	CCLK Direction	Data Width	Serial D_{out}	Configuration Pull-ups
Master-serial mode	0	0	0	Out	1	Yes	No
Boundary-scan mode	1	0	1	N/A	1	No	No
SelectMAP mode	1	1	0	In	8	No	No
Slave-serial mode	1	1	1	In	1	Yes	No
Master-serial mode	1	0	0	Out	1	Yes	Yes

either asserted or de-asserted. Otherwise an abort is initiated, as described below.

2. Drive data onto D[7:0]. Note that to avoid contention, the data source should not be enabled while $\overline{CS}$ is Low and $\overline{WRITE}$ is High. Similarly, while $\overline{WRITE}$ is High, no more that one $\overline{CS}$ should be asserted.
3. At the rising edge of CCLK: If BUSY is Low, the data is accepted on this clock. If BUSY is High (from a previous write), the data is not accepted. Acceptance instead occurs on the first clock after BUSY goes Low, and the data must be held until this has happened.
4. Repeat steps 2 and 3 until all the data has been sent.
5. De-assert $\overline{CS}$ and $\overline{WRITE}$.

Table 11: **SelectMAP Write Timing Characteristics**

	Description		Symbol	Values	Units
CCLK	D_{0-7} Setup/Hold	1/2	T_{SMDCC}/T_{SMCCD}	5.0 / 1.7	ns, min
	$\overline{CS}$ Setup/Hold	3/4	T_{SMCSCC}/T_{SMCCCS}	7.0 / 1.7	ns, min
	$\overline{WRITE}$ Setup/Hold	5/6	T_{SMCCW}/T_{SMWCC}	7.0 / 1.7	ns, min
	BUSY Propagation Delay	7	T_{SMCKBY}	12.0	ns, max
	Maximum Frequency		F_{CC}	66	MHz, max
	Maximum Frequency with no handshake		F_{CCNH}	50	MHz, max



DS022_45_071702

Figure 17: **Write Operations**

A flowchart for the write operation appears in Figure 18. Note that if CCLK is slower than f_{CCNH}, the FPGA never asserts BUSY, In this case, the above handshake is unnecessary, and data can simply be entered into the FPGA every CCLK cycle.

Abort

During a given assertion of $\overline{CS}$, the user cannot switch from a write to a read, or vice-versa. This action causes the current packet command to be aborted. The device remains BUSY until the aborted operation has completed. Following an abort, data is assumed to be unaligned to word boundaries, and the FPGA requires a new synchronization word prior to accepting any new packets.

To initiate an abort during a write operation, de-assert $\overline{WRITE}$. At the rising edge of CCLK, an abort is initiated, as shown in Figure 19.

Port Signals

Each block SelectRAM+ port operates independently of the others while accessing the same set of 4096 memory cells.

Table 15 describes the depth and width aspect ratios for the block SelectRAM+ memory.

Table 15: **Block SelectRAM+ Port Aspect Ratios**

Width	Depth	ADDR Bus	Data Bus
1	4096	ADDR<11:0>	DATA<0>
2	2048	ADDR<10:0>	DATA<1:0>
4	1024	ADDR<9:0>	DATA<3:0>
8	512	ADDR<8:0>	DATA<7:0>
16	256	ADDR<7:0>	DATA<15:0>

Clock—CLK[A|B]

Each port is fully synchronous with independent clock pins. All port input pins have setup time referenced to the port CLK pin. The data output bus has a clock-to-out time referenced to the CLK pin.

Enable—EN[A|B]

The enable pin affects the read, write and reset functionality of the port. Ports with an inactive enable pin keep the output pins in the previous state and do not write data to the memory cells.

Write Enable—WE[A|B]

Activating the write enable pin allows the port to write to the memory cells. When active, the contents of the data input bus are written to the RAM at the address pointed to by the address bus, and the new data also reflects on the data out bus. When inactive, a read operation occurs and the contents of the memory cells referenced by the address bus reflect on the data out bus.

Reset—RST[A|B]

The reset pin forces the data output bus latches to zero synchronously. This does not affect the memory cells of the RAM and does not disturb a write operation on the other port.

Address Bus—ADDR[A|B]<#:0>

The address bus selects the memory cells for read or write. The width of the port determines the required width of this bus as shown in Table 15.

Data In Bus—DI[A|B]<#:0>

The data in bus provides the new data value to be written into the RAM. This bus and the port have the same width, as shown in Table 15.

Data Output Bus—DO[A|B]<#:0>

The data out bus reflects the contents of the memory cells referenced by the address bus at the last active clock edge. During a write operation, the data out bus reflects the data in bus. The width of this bus equals the width of the port. The allowed widths appear in Table 15.

Inverting Control Pins

The four control pins (CLK, EN, WE and RST) for each port have independent inversion control as a configuration option.

Address Mapping

Each port accesses the same set of 4096 memory cells using an addressing scheme dependent on the width of the port. The physical RAM location addressed for a particular width are described in the following formula (of interest only when the two ports use different aspect ratios).

$$\text{Start} = ((\text{ADDR}_{\text{port}} + 1) * \text{Width}_{\text{port}}) - 1$$

$$\text{End} = \text{ADDR}_{\text{port}} * \text{Width}_{\text{port}}$$

Table 16 shows low order address mapping for each port width.

Table 16: **Port Address Mapping**

Port Width	Port Addresses																
1	4095...	15	14	13	12	11	10	09	08	07	06	05	04	03	02	01	00
2	2047...	07		06		05		04		03		02		01		00	
4	1023...	03				02				01				00			
8	511...	01								00							
16	255...	00															

Creating Larger RAM Structures

The block SelectRAM+ columns have specialized routing to allow cascading blocks together with minimal routing delays. This achieves wider or deeper RAM structures with a smaller timing penalty than when using normal routing channels.

Location Constraints

Block SelectRAM+ instances can have LOC properties attached to them to constrain the placement. The block SelectRAM+ placement locations are separate from the CLB location naming convention, allowing the LOC properties to transfer easily from array to array.

The LOC properties use the following form.

LOC = RAMB4_R#C#

RAMB4_R0C0 is the upper left RAMB4 location on the device.

Conflict Resolution

The block SelectRAM+ memory is a true dual-read/write port RAM that allows simultaneous access of the same memory cell from both ports. When one port writes to a given memory cell, the other port must not address that memory cell (for a write or a read) within the clock-to-clock setup window. The following lists specifics of port and memory cell write conflict resolution.

- If both ports write to the same memory cell simultaneously, violating the clock-to-clock setup requirement, consider the data stored as invalid.
- If one port attempts a read of the same memory cell the other simultaneously writes, violating the clock-to-clock setup requirement, the following occurs.
  - The write succeeds
  - The data out on the writing port accurately reflects the data written.
  - The data out on the reading port is invalid.

Conflicts do not cause any physical damage.

Single Port Timing

Figure 33 shows a timing diagram for a single port of a block SelectRAM+ memory. The block SelectRAM+ AC switching characteristics are specified in the data sheet. The block SelectRAM+ memory is initially disabled.

At the first rising edge of the CLK pin, the ADDR, DI, EN, WE, and RST pins are sampled. The EN pin is High and the WE pin is Low indicating a read operation. The DO bus contains the contents of the memory location, 0x00, as indicated by the ADDR bus.

At the second rising edge of the CLK pin, the ADDR, DI, EN, WR, and RST pins are sampled again. The EN and WE pins are High indicating a write operation. The DO bus mirrors the DI bus. The DI bus is written to the memory location 0x0F.

At the third rising edge of the CLK pin, the ADDR, DI, EN, WR, and RST pins are sampled again. The EN pin is High and the WE pin is Low indicating a read operation. The DO bus contains the contents of the memory location 0x7E as indicated by the ADDR bus.

At the fourth rising edge of the CLK pin, the ADDR, DI, EN, WR, and RST pins are sampled again. The EN pin is Low indicating that the block SelectRAM+ memory is now disabled. The DO bus retains the last value.

Dual Port Timing

Figure 34 shows a timing diagram for a true dual-port read/write block SelectRAM+ memory. The clock on port A has a longer period than the clock on Port B. The timing parameter T_{BCCS}, (clock-to-clock set-up) is shown on this diagram. The parameter, T_{BCCS} is violated once in the diagram. All other timing parameters are identical to the single port version shown in Figure 33.

T_{BCCS} is only of importance when the address of both ports are the same and at least one port is performing a write operation. When the clock-to-clock set-up parameter is violated for a WRITE-WRITE condition, the contents of the memory at that location are invalid. When the clock-to-clock set-up parameter is violated for a WRITE-READ condition, the contents of the memory are correct, but the read port has invalid data. At the first rising edge of CLKA, memory location 0x00 is to be written with the value 0xAAAA and is mirrored on the DOA bus. The last operation of Port B was a read to the same memory location 0x00. The DOB bus of Port B does not change with the new value on Port A, and retains the last read value. A short time later, Port B executes another read to memory location 0x00, and the DOB bus now reflects the new memory value written by Port A.

At the second rising edge of CLKA, memory location 0x7E is written with the value 0x9999 and is mirrored on the DOA bus. Port B then executes a read operation to the same memory location without violating the T_{BCCS} parameter and the DOB reflects the new memory values written by Port A.

Initialization

The block SelectRAM+ memory can initialize during the device configuration sequence. The 16 initialization properties of 64 hex values each (a total of 4096 bits) set the initialization of each RAM. These properties appear in Table 17. Any initialization properties not explicitly set configure as zeros. Partial initialization strings pad with zeros. Initialization strings greater than 64 hex values generate an error. The RAMs can be simulated with the initialization values using generics in VHDL simulators and parameters in Verilog simulators.

Initialization in VHDL and Synopsys

The block SelectRAM+ structures can be initialized in VHDL for both simulation and synthesis for inclusion in the EDIF output file. The simulation of the VHDL code uses a generic to pass the initialization. Synopsys FPGA compiler does not presently support generics. The initialization values instead attach as attributes to the RAM by a built-in Synopsys dc_script. The translate_off statement stops synthesis translation of the generic statements. The following code illustrates a module that employs these techniques.

Table 17: **RAM Initialization Properties**

Property	Memory Cells
INIT_00	255 to 0
INIT_01	511 to 256
INIT_02	767 to 512
INIT_03	1023 to 768
INIT_04	1279 to 1024
INIT_05	1535 to 1280
INIT_06	1791 to 2047
INIT_07	2047 to 1792
INIT_08	2303 to 2048
INIT_09	2559 to 2304
INIT_0a	2815 to 2560
INIT_0b	3071 to 2816
INIT_0c	3327 to 3072
INIT_0d	3583 to 3328
INIT_0e	3839 to 3584
INIT_0f	4095 to 3840

Initialization in Verilog and Synopsys

The block SelectRAM+ structures can be initialized in Verilog for both simulation and synthesis for inclusion in the EDIF output file. The simulation of the Verilog code uses a defparam to pass the initialization. The Synopsys FPGA compiler does not presently support defparam. The initialization values instead attach as attributes to the RAM by a built-in Synopsys dc_script. The translate_off statement stops synthesis translation of the defparam statements. The following code illustrates a module that employs these techniques.

Design Examples

Creating a 32-bit Single-Port RAM

The true dual-read/write port functionality of the block SelectRAM+ memory allows a single port, 128 deep by 32-bit wide RAM to be created using a single block SelectRAM+ cell as shown inTable 35.

Interleaving the memory space, setting the LSB of the address bus of Port A to 1 (V_{CC}), and the LSB of the address bus of Port B to 0 (GND), allows a 32-bit wide single port RAM to be created.

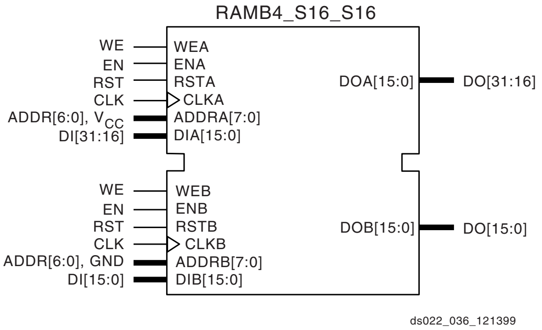


Figure 35: **Single Port 128 x 32 RAM**

Creating Two Single-Port RAMs

The true dual-read/write port functionality of the block SelectRAM+ memory allows a single RAM to be split into two single port memories of 2K bits each as shown in Figure 36.

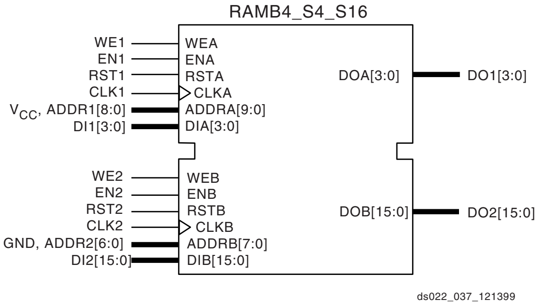


Figure 36: **512 x 4 RAM and 128 x 16 RAM**

In this example, a 512K x 4 RAM (Port A) and a 128 x 16 RAM (Port B) are created out of a single block SelectRAM+. The address space for the RAM is split by fixing the MSB of Port A to 1 (V_{CC}) for the upper 2K bits and the MSB of Port B to 0 (GND) for the lower 2K bits.

Block Memory Generation

The CoreGen program generates memory structures using the block SelectRAM+ features. This program outputs VHDL or Verilog simulation code templates and an EDIF file for inclusion in a design.

Virtex-E Extended Memory Data Sheet

The Virtex-E Extended Memory Data Sheet contains the following modules:

- DS025-1, Virtex-E 1.8V Extended Memory FPGAs: Introduction and Ordering Information (Module 1)
- DS025-2, Virtex-E 1.8V Extended Memory FPGAs: **Functional Description (Module 2)**
- DS025-3, Virtex-E 1.8V Extended Memory FPGAs: DC and Switching Characteristics (Module 3)
- DS025-4, Virtex-E 1.8V Extended Memory FPGAs: Pinout Tables (Module 4)

LVDS DC Specifications

DC Parameter	Symbol	Conditions	Min	Typ	Max	Units
Supply Voltage	V_{CCO}		2.375	2.5	2.625	V
Output High Voltage for Q and $\overline{Q}$	V_{OH}	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.25	1.425	1.6	V
Output Low Voltage for Q and $\overline{Q}$	V_{OL}	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.9	1.075	1.25	V
Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	V_{ODIFF}	R_T = 100 Ω across Q and $\overline{Q}$ signals	250	350	450	mV
Output Common-Mode Voltage	V_{OCM}	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.125	1.25	1.375	V
Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	V_{IDIFF}	Common-mode input voltage = 1.25 V	100	350	NA	mV
Input Common-Mode Voltage	V_{ICM}	Differential input voltage = ±350 mV	0.2	1.25	2.2	V

Notes:

1. Refer to the Design Consideration section for termination schematics.

LVPECL DC Specifications

These values are valid at the output of the source termination pack shown under LVPECL, with a 100 Ω differential load only. The V_{OH} levels are 200 mV below standard LVPECL levels and are compatible with devices tolerant of lower common-mode ranges. The following table summarizes the DC output specifications of LVPECL.

DC Parameter	Min	Max	Min	Max	Min	Max	Units
V_{CCO}	**3.0**		**3.3**		**3.6**		**V**
V_{OH}	1.8	2.11	1.92	2.28	2.13	2.41	V
V_{OL}	0.96	1.27	1.06	1.43	1.30	1.57	V
V_{IH}	1.49	2.72	1.49	2.72	1.49	2.72	V
V_{IL}	0.86	2.125	0.86	2.125	0.86	2.125	V
Differential Input Voltage	0.3	-	0.3	-	0.3	-	V

Virtex-E Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values. For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer (TRCE in the Xilinx Development System) and back-annotated to the simulation net list. All timing parameters assume worst-case operating conditions (supply voltage and junction temperature). Values apply to all Virtex-E devices unless otherwise noted.

IOB Input Switching Characteristics

Input delays associated with the pad are specified for LVTTL levels. For other standards, adjust the delays with the values shown in "IOB Input Switching Characteristics Standard Adjustments" on page 6.

			Speed Grade(2)				
Description(1)	**Symbol**	**Device**	**Min**	**-8**	**-7**	**-6**	**Units**
Propagation Delays							
Pad to I output, no delay	T_{IOPI}	All	0.43	0.8	0.8	0.8	ns, max
Pad to I output, with delay	T_{IOPID}	XCV405E	0.51	1.0	1.0	1.0	ns, max
		XCV812E	0.55	1.1	1.1	1.1	ns, max
Pad to output IQ via transparent latch, no delay	T_{IOPLI}	All	0.75	1.4	1.5	1.6	ns, max
Pad to output IQ via transparent latch, with delay	T_{IOPLID}	XCV405E	1.55	3.5	3.6	3.7	ns, max
		XCV812E	1.55	3.5	3.6	3.7	ns, max
Propagation Delays							
Clock							
Minimum Pulse Width, High	T_{CH}	All	0.56	1.2	1.3	1.4	ns, min
Minimum Pulse Width, Low	T_{CL}		0.56	1.2	1.3	1.4	ns, min
Clock CLK to output IQ	T_{IOCKIQ}		0.18	0.4	0.7	0.7	ns, max
Setup and Hold Times with respect to Clock at IOB Input Register							
Pad, no delay	T_{IOPICK} / T_{IOICKP}	All	0.69 / 0	1.3 / 0	1.4 / 0	1.5 / 0	ns, min
Pad, with delay	$T_{IOPICKD}$ / $T_{IOICKPD}$	XCV405E	1.49 / 0	3.4 / 0	3.5 / 0	3.5 / 0	ns, min
		XCV812E	1.49 / 0	3.4 / 0	3.5 / 0	3.5 / 0	ns, min
ICE input	$T_{IOICECK}$ / $T_{IOCKICE}$	All	0.28 / 0.0	0.55 / 0.01	0.7 / 0.01	0.7 / 0.01	ns, min
SR input (IFF, synchronous)	$T_{IOSRCKI}$	All	0.38	0.8	0.9	1.0	ns, min
Set/Reset Delays							
SR input to IQ (asynchronous)	T_{IOSRIQ}	All	0.54	1.1	1.2	1.4	ns, max
GSR to output IQ	T_{GSRQ}	All	3.88	7.6	8.5	9.7	ns, max

Notes:

1. A Zero "0" Hold Time listing indicates no hold time or a negative hold time. Negative values can not be guaranteed "best-case", but if a "0" is listed, there is no positive hold time.
2. Input timing i for LVTTL is measured at 1.4 V. For other I/O standards, see Table 3.

Calculation of T_{ioop} as a Function of Capacitance

T_{ioop} is the propagation delay from the O Input of the IOB to the pad. The values for T_{ioop} are based on the standard capacitive load (Csl) for each I/O standard as listed in Table 2.

Table 2: **Constants for Use in Calculation of T_{ioop}**

Standard	Csl (pF)	fl (ns/pF)
LVTTL Fast Slew Rate, 2mA drive	35	0.41
LVTTL Fast Slew Rate, 4mA drive	35	0.20
LVTTL Fast Slew Rate, 6mA drive	35	0.13
LVTTL Fast Slew Rate, 8mA drive	35	0.079
LVTTL Fast Slew Rate, 12mA drive	35	0.044
LVTTL Fast Slew Rate, 16mA drive	35	0.043
LVTTL Fast Slew Rate, 24mA drive	35	0.033
LVTTL Slow Slew Rate, 2mA drive	35	0.41
LVTTL Slow Slew Rate, 4mA drive	35	0.20
LVTTL Slow Slew Rate, 6mA drive	35	0.10
LVTTL Slow Slew Rate, 8mA drive	35	0.086
LVTTL Slow Slew Rate, 12mA drive	35	0.058
LVTTL Slow Slew Rate, 16mA drive	35	0.050
LVTTL Slow Slew Rate, 24mA drive	35	0.048
LVCMOS2	35	0.041
LVCMOS18	35	0.050
PCI 33 MHZ 3.3 V	10	0.050
PCI 66 MHz 3.3 V	10	0.033
GTL	0	0.014
GTL+	0	0.017
HSTL Class I	20	0.022
HSTL Class III	20	0.016
HSTL Class IV	20	0.014
SSTL2 Class I	30	0.028
SSTL2 Class II	30	0.016
SSTL3 Class I	30	0.029
SSTL3 Class II	30	0.016
CTT	20	0.035
AGP	10	0.037

Notes:

1. I/O parameter measurements are made with the capacitance values shown above. See the Application Examples for appropriate terminations.
2. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

For other capacitive loads, use the formulas below to calculate the corresponding T_{ioop}.

$$T_{ioop} = T_{ioop} + T_{opadjust} + (C_{load} - C_{sl}) * fl$$

where:

$T_{opadjust}$ is reported above in the Output Delay Adjustment section.

C_{load} is the capacitive load for the design.

Table 3: **Delay Measurement Methodology**

Standard	V_L[1]	V_H[1]	Meas. Point	V_{REF} (Typ)[2]
LVTTL	0	3	1.4	-
LVCMOS2	0	2.5	1.125	-
PCI33_3	Per PCI Spec			-
PCI66_3	Per PCI Spec			-
GTL	V_{REF} –0.2	V_{REF} +0.2	V_{REF}	0.80
GTL+	V_{REF} –0.2	V_{REF} +0.2	V_{REF}	1.0
HSTL Class I	V_{REF} –0.5	V_{REF} +0.5	V_{REF}	0.75
HSTL Class III	V_{REF} –0.5	V_{REF} +0.5	V_{REF}	0.90
HSTL Class IV	V_{REF} –0.5	V_{REF} +0.5	V_{REF}	0.90
SSTL3 I & II	V_{REF} –1.0	V_{REF} +1.0	V_{REF}	1.5
SSTL2 I & II	V_{REF} –0.75	V_{REF} +0.75	V_{REF}	1.25
CTT	V_{REF} –0.2	V_{REF} +0.2	V_{REF}	1.5
AGP	V_{REF} – $(0.2xV_{CCO})$	V_{REF} + $(0.2xV_{CCO})$	V_{REF}	Per AGP Spec
LVDS	1.2 – 0.125	1.2 + 0.125	1.2	
LVPECL	1.6 – 0.3	1.6 + 0.3	1.6	

Notes:

1. Input waveform switches between V_L and V_H.
2. Measurements are made at V_{REF} (Typ), Maximum, and Minimum. Worst-case values are reported.

   I/O parameter measurements are made with the capacitance values shown in Table 2. See the Application Examples for appropriate terminations.

   I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

Clock Distribution Switching Characteristics

Description	Symbol	Speed Grade				Units
		Min	-8	-7	-6	
GCLK IOB and Buffer						
Global Clock PAD to output.	T_{GPIO}	0.38	0.7	0.7	0.7	ns, max
Global Clock Buffer I input to O output	T_{GIO}	0.11	0.19	0.45	0.50	ns, max

I/O Standard Global Clock Input Adjustments

Description[1]	Symbol	Standard	Speed Grade				Units
			Min	-8	-7	-6	
Data Input Delay Adjustments							
Standard-specific global clock input delay adjustments	$T_{GPLVTTL}$	LVTTL	0.0	0.0	0.0	0.0	ns, max
	$T_{GPLVCMOS2}$	LVCMOS2	–0.02	0.0	0.0	0.0	ns, max
	$T_{GPLVCMOS18}$	LVCMOS2	0.12	0.20	0.20	0.20	ns, max
	T_{GLVDS}	LVDS	0.23	0.38	0.38	0.38	ns, max
	$T_{GLVPECL}$	LVPECL	0.23	0.38	0.38	0.38	ns, max
	$T_{GPPCI33\_3}$	PCI, 33 MHz, 3.3 V	–0.05	0.08	0.08	0.08	ns, max
	$T_{GPPCI66\_3}$	PCI, 66 MHz, 3.3 V	–0.05	–0.11	–0.11	–0.11	ns, max
	T_{GPGTL}	GTL	0.20	0.37	0.37	0.37	ns, max
	T_{GPGTLP}	GTL+	0.20	0.37	0.37	0.37	ns, max
	T_{GPHSTL}	HSTL	0.18	0.27	0.27	0.27	ns, max
	$T_{GPSSTL2}$	SSTL2	0.21	0.27	0.27	0.27	ns, max
	$T_{GPSSTL3}$	SSTL3	0.18	0.27	0.27	0.27	ns, max
	T_{GPCTT}	CTT	0.22	0.33	0.33	0.33	ns, max
	T_{GPAGP}	AGP	0.21	0.27	0.27	0.27	ns, max

Notes:

1. Input timing for GPLVTTL is measured at 1.4 V. For other I/O standards, see Table 3.

Virtex-E Pin-to-Pin Output Parameter Guidelines

All devices are 100% functionally tested. Listed below are representative values for typical pin locations and normal clock loading. Values are expressed in nanoseconds unless otherwise noted.

Global Clock Input to Output Delay for LVTTL, 12 mA, Fast Slew Rate, *with* DLL

Description(1)	Symbol	Device(3)	Speed Grade(2)				Units
			Min	-8	-7	-6	
LVTTL Global Clock Input to Output Delay using Output Flip-flop, 12 mA, Fast Slew Rate, *with* DLL. For data *output* with different standards, adjust the delays with the values shown in "IOB Output Switching Characteristics Standard Adjustments" on page 8.	$T_{ICKOFDLL}$	XCV405E	1.0	3.1	3.1	3.1	ns
		XCV812E	1.0	3.1	3.1	3.1	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Output timing is measured at 50% V_{CC} threshold with 35 pF external capacitive load. For other I/O standards and different loads, see Table 2 and Table 3.
3. DLL output jitter is already included in the timing calculation.

Global Clock Input to Output Delay for LVTTL, 12 mA, Fast Slew Rate, *without* DLL

Description(1)	Symbol	Device	Speed Grade(2)				Units
			Min	-8	-7	-6	
LVTTL Global Clock Input to Output Delay using Output Flip-flop, 12 mA, Fast Slew Rate, *without* DLL. For data *output* with different standards, adjust the delays with the values shown in "IOB Output Switching Characteristics Standard Adjustments" on page 8.	T_{ICKOF}	XCV405E	1.6	4.5	4.7	4.9	ns
		XCV812E	1.8	4.8	5.0	5.2	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Output timing is measured at 50% V_{CC} threshold with 35 pF external capacitive load. For other I/O standards and different loads, see Table 2 and Table 3.

DLL Clock Tolerance, Jitter, and Phase Information

All DLL output jitter and phase specifications determined through statistical measurement at the package pins using a clock mirror configuration and matched drivers.

			CLKDLLHF		CLKDLL		
Description	**Symbol**	**F_{CLKIN}**	**Min**	**Max**	**Min**	**Max**	**Units**
Input Clock Period Tolerance	T_{IPTOL}		-	1.0	-	1.0	ns
Input Clock Jitter Tolerance (Cycle to Cycle)	T_{IJITCC}		-	± 150	-	± 300	ps
Time Required for DLL to Acquire Lock(6)	T_{LOCK}	> 60 MHz	-	20	-	20	µs
		50 - 60 MHz	-	-	-	25	µs
		40 - 50 MHz	-	-	-	50	µs
		30 - 40 MHz	-	-	-	90	µs
		25 - 30 MHz	-	-	-	120	µs
Output Jitter (cycle-to-cycle) for any DLL Clock Output(1)	T_{OJITCC}			± 60		± 60	ps
Phase Offset between CLKIN and CLKO(2)	T_{PHIO}			± 100		± 100	ps
Phase Offset between Clock Outputs on the DLL(3)	T_{PHOO}			± 140		± 140	ps
Maximum Phase Difference between CLKIN and CLKO(4)	T_{PHIOM}			± 160		± 160	ps
Maximum Phase Difference between Clock Outputs on the DLL(5)	T_{PHOOM}			± 200		± 200	ps

Notes:

1. **Output Jitter** is cycle-to-cycle jitter measured on the DLL output clock and is based on a maximum tap delay resolution, *excluding* input clock jitter.
2. **Phase Offset between CLKIN and CLKO** is the worst-case fixed time difference between rising edges of CLKIN and CLKO, *excluding* Output Jitter and input clock jitter.
3. **Phase Offset between Clock Outputs on the DLL** is the worst-case fixed time difference between rising edges of any two DLL outputs, *excluding* Output Jitter and input clock jitter.
4. **Maximum Phase Difference between CLKIN an CLKO** is the sum of Output Jitter and Phase Offset between CLKIN and CLKO, or the greatest difference between CLKIN and CLKO rising edges due to DLL alone (*excluding* input clock jitter).
5. **Maximum Phase DIfference between Clock Outputs on the DLL** is the sum of Output JItter and Phase Offset between any DLL clock outputs, or the greatest difference between any two DLL output rising edges sue to DLL alone (*excluding* input clock jitter).
6. Add 30% to the value for Industrial grade parts.

Revision History

The following table shows the revision history for this document.

Date	Version	Revision
03/23/00	1.0	Initial Xilinx release.
08/01/00	1.1	Accumulated edits and fixes. Upgrade to Preliminary. Preview -8 numbers added. Reformatted to adhere to corporate documentation style guidelines. Minor changes in BG560 pin-out table.
09/19/00	1.2	• In Table 3 (Module 4), **FG676 Fine-Pitch BGA — XCV405E**, the following pins are no longer labeled as VREF: B7, G16, G26, W26, AF20, AF8, Y1, H1. • Min values added to **Virtex-E Electrical Characteristics** tables.

Table 3: **FG676 Fine-Pitch BGA — XCV405E**

Bank	Pin Description	Pin #
2	IO_L58P_YY	H25
2	IO_L58N_YY	K23
2	IO_L59P_Y	L20
2	IO_L59N_Y	J26
2	IO_L60P_Y	K25
2	IO_L60N_Y	L22
2	IO_L61P_Y	L21
2	IO_L61N_Y	L23
2	IO_L62P_Y	M20
2	IO_L62N_Y	L24
2	IO_VREF_L63P_YY	M23
2	IO_D3_L63N_YY	M22
2	IO_L64P_YY	L26
2	IO_L64N_YY	M21
2	IO_L65P_Y	N19
2	IO_L65N_Y	M24
2	IO_VREF_L66P_Y	M26
2	IO_L66N_Y	N20
2	IO_L67P_YY	N24
2	IO_L67N_YY	N21
2	IO_L68P_YY	N23
2	IO_L68N_YY	N22
3	IO	P24
3	IO	W25
3	IO	Y26
3	IO	AB25
3	IO	AC26
3	IO_L69P_YY	P21
3	IO_L69N_YY	P23
3	IO_L70P_Y	P22
3	IO_VREF_L70N_Y	R25
3	IO_L71P_Y	P19
3	IO_L71N_Y	P20
3	IO_L72P_YY	R21
3	IO_L72N_YY	R22
3	IO_D4_L73P_YY	R24
3	IO_VREF_L73N_YY	R23
3	IO_L74P_Y	T24
3	IO_L74N_Y	R20
3	IO_L75P_Y	T22
3	IO_L75N_Y	U24
3	IO_L76P_Y	T23
3	IO_L76N_Y	U25
3	IO_L77P_Y	T21
3	IO_L77N_Y	U20
3	IO_L78P_YY	U22
3	IO_L78N_YY	V26
3	IO_L79P_YY	T20
3	IO_D5_L79N_YY	U23
3	IO_D6_L80P_YY	V24
3	IO_VREF_L80N_YY	U21
3	IO_L81P_YY	V23
3	IO_L81N_YY	W24
3	IO_L82P_Y	V22
3	IO_L82N_Y	W26
3	IO_L83P_Y	Y25
3	IO_L83N_Y	V21
3	IO_L84P_YY	V20
3	IO_L84N_YY	AA26
3	IO_L85P_YY	Y24
3	IO_VREF_L85N_YY	W23
3	IO_L86P_Y	AA24
3	IO_L86N_Y	Y23
3	IO_L87P_Y	AB26
3	IO_L87N_Y	W21
3	IO_L88P_Y	Y22
3	IO_VREF_L88N_Y	W22
3	IO_L89P_Y	AA23
3	IO_L89N_Y	AB24

Table 4: **FG676 Fine-Pitch BGA Differential Pin Pair Summary — XCV405E**

Pair	Bank	P Pin	N Pin	AO	Other Functions
50	2	F23	G23	√	-
51	2	H23	J20	√	VREF
52	2	G24	H22	√	-
53	2	J21	G25	2	-
54	2	G26	J22	1	-
55	2	H24	J23	√	-
56	2	J24	K20	√	VREF
57	2	K22	K21	√	D2
58	2	H25	K23	√	-
59	2	L20	J26	2	-
60	2	K25	L22	1	-
61	2	L21	L23	1	-
62	2	M20	L24	1	-
63	2	M23	M22	√	D3
64	2	L26	M21	√	-
65	2	N19	M24	2	-
66	2	M26	N20	1	VREF
67	2	N24	N21	√	-
68	2	N23	N22	√	-
69	3	P21	P23	√	-
70	3	P22	R25	1	VREF
71	3	P19	P20	2	-
72	3	R21	R22	√	-
73	3	R24	R23	√	VREF
74	3	T24	R20	1	-
75	3	T22	U24	1	-
76	3	T23	U25	1	-
77	3	T21	U20	2	-
78	3	U22	V26	√	-
79	3	T20	U23	√	D5
80	3	V24	U21	√	VREF
81	3	V23	W24	√	-
82	3	V22	W26	NA	-
83	3	Y25	V21	NA	-
84	3	V20	AA26	√	-
85	3	Y24	W23	√	VREF
86	3	AA24	Y23	NA	-
87	3	AB26	W21	NA	-
88	3	Y22	W22	NA	VREF
89	3	AA23	AB24	NA	-
90	3	W20	AC24	√	-
91	3	AB23	Y21	√	INIT
92	4	AC22	AD26	√	-
93	4	AD23	AA20	NA1	-
94	4	Y19	AC21	√	-
95	4	AD22	AB20	√	VREF
96	4	AE22	Y18	NA	-
97	4	AF22	AA19	NA	-
98	4	AD21	AB19	√	VREF
99	4	AC20	AA18	√	-
100	4	AC19	AD20	NA	-
101	4	AF20	AB18	NA	-
102	4	AD19	Y17	NA	-
103	4	AE19	AD18	NA	VREF
104	4	AF19	AA17	√	-
105	4	AC17	AB17	NA	-
106	4	Y16	AE17	√	-
107	4	AF17	AA16	√	-
108	4	AD17	AB16	NA	-
109	4	AC16	AD16	√	-
110	4	AC15	Y15	√	VREF
111	4	AD15	AA15	√	-
112	4	W14	AB15	NA	-
113	4	AF15	Y14	NA	VREF
114	4	AD14	AB14	NA	-
115	5	AC14	AF13	NA	IO_LVDS_DLL
116	5	AA13	AF12	NA	VREF
117	5	AC13	W13	NA	-

Table 5: **FG900 Fine-Pitch BGA Package — XCV812E**

Bank	Description	Pin
0	IO_L29N	D14
0	IO_L29P	B14
0	IO_L30N_YY	A14
0	IO_L30P_YY	J14
0	IO_VREF_L31N_YY	K14
0	IO_L31P_YY	J15
0	IO_LVDS_DLL_L34N	A15
1	GCk2	E15
1	IO	B18
1	IO	B21
1	IO	B28
1	IO	C23
1	IO	C26
1	IO	D20
1	IO	D23
1	IO_LVDS_DLL_L34P	E16
1	IO_L35N	B16
1	IO_L35P	F16
1	IO_L36N	A16
1	IO_L36P	H16
1	IO_L37N_YY	C16
1	IO_VREF_L37P_YY	K15
1	IO_L38N_YY	K16
1	IO_L38P_YY	G16
1	IO_L39N	A17
1	IO_L39P	E17
1	IO_L40N	F17
1	IO_L40P	C17
1	IO_L41N_YY	E18
1	IO_VREF_L41P_YY	A18
1	IO_L42N_YY	D18
1	IO_L42P_YY	A19
1	IO_L43N	B19

Table 5: **FG900 Fine-Pitch BGA Package — XCV812E**

Bank	Description	Pin
1	IO_L43P	G18
1	IO_L44N	D19
1	IO_L44P	H18
1	IO_L45N_YY	F18
1	IO_VREF_L45P_YY	F19
1	IO_L46N_YY	B20
1	IO_L46P_YY	K17
1	IO_L48N_Y	G19
1	IO_L48P_Y	C20
1	IO_L49N_Y	K18
1	IO_L49P_Y	E20
1	IO_L51N_YY	F20
1	IO_L51P_YY	A21
1	IO_L52N_YY	C21
1	IO_VREF_L52P_YY	A22
1	IO_L53N	H19
1	IO_L53P	B22
1	IO_L54N	E21
1	IO_L54P	D22
1	IO_L55N_YY	F21
1	IO_VREF_L55P_YY	C22
1	IO_L56N_YY	H20
1	IO_L56P_YY	E22
1	IO_L57N	G21
1	IO_L57P	A23
1	IO_L58N	A24
1	IO_L58P	K19
1	IO_L59N_YY	C24
1	IO_VREF_L59P_YY	B24
1	IO_L60N_YY	H21
1	IO_L60P_YY	G22
1	IO_L61N	E23
1	IO_L61P	C25
1	IO_L62N	D24

Table 5: **FG900 Fine-Pitch BGA Package — XCV812E**

Bank	Description	Pin
3	IO_L131P_YY	Y22
3	IO_VREF_L131N_YY	AC27
3	IO_L132P	AD28
3	IO_L132N	AB25
3	IO_L133P	AC26
3	IO_L133N	AE30
3	IO_L134P_YY	AD27
3	IO_L134N_YY	AF30
3	IO_L135P_Y	AF29
3	IO_VREF_L135N_Y	AB24
3	IO_L136P	AB23
3	IO_L136N	AE28
3	IO_L138P	AE26
3	IO_L138N	AG29
3	IO_L139P_Y	AH30
3	IO_L139N_Y	AC24
3	IO_D7_L141P_YY	AH29
3	IO_INIT_L141N_YY	AA22
4	GCK0	AJ16
4	IO	AB19
4	IO	AC16
4	IO	AC19
4	IO	AD19
4	IO	AD20
4	IO	AE21
4	IO	AF19
4	IO	AH17
4	IO	AH23
4	IO	AH26
4	IO	AH27
4	IO	AK18
4	IO_VREF_4	AA18
4	IO_L142P_YY	AF27
4	IO_L142N_YY	AK28
4	IO_L144P_Y	AD23
4	IO_L144N_Y	AJ27
4	IO_L145P_Y	AB21
4	IO_L145N_Y	AF25
4	IO_L147P_YY	AA21
4	IO_L147N_YY	AG25
4	IO_VREF_4_L148P_YY	AJ26
4	IO_L148N_YY	AD22
4	IO_L149P	AA20
4	IO_L149N	AH25
4	IO_L150P	AC21
4	IO_L150N	AF24
4	IO_L151P_YY	AG24
4	IO_L151N_YY	AK26
4	IO_VREF_4_L152P_YY	AJ24
4	IO_L152N_YY	AF23
4	IO_L153P	AE23
4	IO_L153N	AB20
4	IO_L154P	AC20
4	IO_L154N	AG23
4	IO_L155P_YY	AF22
4	IO_L155N_YY	AE22
4	IO_VREF_4_L156P_YY	AJ22
4	IO_L156N_YY	AG22
4	IO_L158P	AA19
4	IO_L158N	AF21
4	IO_L160P	AG21
4	IO_L160N	AK23
4	IO_L162P_Y	AE20
4	IO_L162N_Y	AJ21
4	IO_L163P_Y	AG20
4	IO_L163N_Y	AF20
4	IO_L165P_YY	AJ20

Table 5: **FG900 Fine-Pitch BGA Package — XCV812E**

Bank	Description	Pin
NA	VCCINT	V16
NA	VCCINT	V17
NA	VCCINT	V18
NA	VCCINT	W11
NA	VCCINT	W12
NA	VCCINT	W19
NA	VCCINT	W20
NA	VCCINT	Y11
NA	VCCINT	Y12
NA	VCCINT	Y19
NA	VCCINT	Y20
NA	VCCO_0	B6
NA	VCCO_0	M15
NA	VCCO_0	M14
NA	VCCO_0	L15
NA	VCCO_0	L14
NA	VCCO_0	H14
NA	VCCO_0	M13
NA	VCCO_0	C12
NA	VCCO_1	B25
NA	VCCO_1	C19
NA	VCCO_1	M18
NA	VCCO_1	M17
NA	VCCO_1	L17
NA	VCCO_1	H17
NA	VCCO_1	L16
NA	VCCO_1	M16
NA	VCCO_2	F29
NA	VCCO_2	M28
NA	VCCO_2	P23
NA	VCCO_2	R20
NA	VCCO_2	P20
NA	VCCO_2	R19
NA	VCCO_2	N19
NA	VCCO_2	P19
NA	VCCO_3	AE29
NA	VCCO_3	W28
NA	VCCO_3	U23
NA	VCCO_3	U20
NA	VCCO_3	T20
NA	VCCO_3	V19
NA	VCCO_3	T19
NA	VCCO_3	U19
NA	VCCO_4	AJ25
NA	VCCO_4	AH19
NA	VCCO_4	W18
NA	VCCO_4	AC17
NA	VCCO_4	Y17
NA	VCCO_4	W17
NA	VCCO_4	W16
NA	VCCO_4	Y16
NA	VCCO_5	AJ6
NA	VCCO_5	Y15
NA	VCCO_5	W15
NA	VCCO_5	AC14
NA	VCCO_5	Y14
NA	VCCO_5	W14
NA	VCCO_5	W13
NA	VCCO_5	AH12
NA	VCCO_6	AE2
NA	VCCO_6	V12
NA	VCCO_6	U12
NA	VCCO_6	T12
NA	VCCO_6	U11
NA	VCCO_6	T11
NA	VCCO_6	U8
NA	VCCO_6	W3

Virtex-E Extended Memory Device/Package Combinations and Maximum I/O

Virtex-E Extended Memory Series Maximum User I/O by Device/Package (Excluding Dedicated Clock Pins)

Package	XCV405E	XCV812E
BG560	404	404
FG676	404	
FG900		556

Virtex-E Ordering Information

Virtex-II ordering information is shown in Figure 1

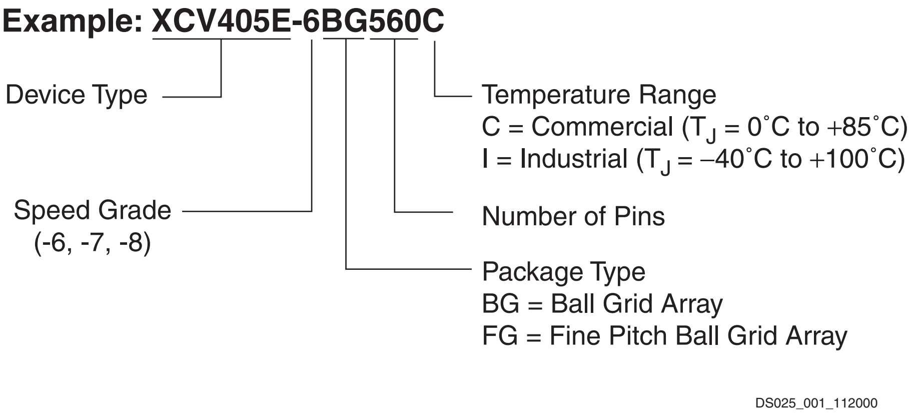


Figure 1: **Virtex Ordering Information**